

PSMN2R2-40PS-VB Datasheet

N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS}	40	V
$R_{DS(on)}$ $V_{GS} = 10\text{ V}$	2	$m\Omega$
I_D	180	A
Configuration	Single	

FEATURES

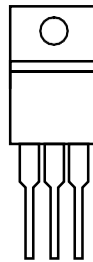
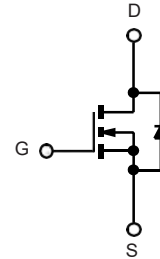
- Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Synchronous Rectification
- Power Supplies



TO-220AB

G D S
Top View

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175\text{ }^\circ\text{C}$)	$T_C = 25\text{ }^\circ\text{C}$	I_D	180 ^{a, c}
	$T_C = 70\text{ }^\circ\text{C}$		150 ^c
	$T_A = 25\text{ }^\circ\text{C}$		29 ^b
	$T_A = 70\text{ }^\circ\text{C}$		23 ^b
Pulsed Drain Current	I_{DM}	350	A
Avalanche Current Pulse	I_{AS}	80	
Single Pulse Avalanche Energy	E_{AS}	320	
Continuous Source-Drain Diode Current	$T_C = 25\text{ }^\circ\text{C}$	I_S	110 ^{a, c}
	$T_A = 25\text{ }^\circ\text{C}$		2.6 ^b
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	312 ^a
	$T_C = 70\text{ }^\circ\text{C}$		200
	$T_A = 25\text{ }^\circ\text{C}$		3.13 ^b
	$T_A = 70\text{ }^\circ\text{C}$		2.0 ^b
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	32	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	0.33	0.4	

Notes:

a. Based on $T_C = 25\text{ }^\circ\text{C}$.

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40			V
V _{DS} Temperature Coefficient	Δ V _{DS} /T _J	I _D = 250 μA		41		mV/°C
V _{GS(th)} Temperature Coefficient	Δ V _{GS(th)} /T _J			- 8		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			1	μA
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		2		mΩ
		V _{GS} = 4.5 V, I _D = 20 A		15		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A		180		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz		9000		pF
Output Capacitance	C _{oss}			650		
Reverse Transfer Capacitance	C _{rss}			450		
Total Gate Charge	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 20 A		120		nC
Gate-Source Charge	Q _{gs}			30		
Gate-Drain Charge	Q _{gd}			16		
Gate Resistance	R _g	f = 1 MHz		0.85	1.3	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 20 V, R _L = 1.0 Ω I _D ≅ 20 A, V _{GEN} = 10 V, R _g = 1 Ω		20	30	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			77	115	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 20 V, R _L = 1.0 Ω I _D ≅ 20 A, V _{GEN} = 4.5 V, R _g = 1 Ω		102	155	
Rise Time	t _r			62	95	
Turn-Off Delay Time	t _{d(off)}			180	270	
Fall Time	t _f			60	90	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			110	A
Pulse Diode Forward Current ^a	I _{SM}				200	
Body Diode Voltage	V _{SD}	I _S = 20 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		50	75	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70	105	nC
Reverse Recovery Fall Time	t _a			30		ns
Reverse Recovery Rise Time	t _b			20		

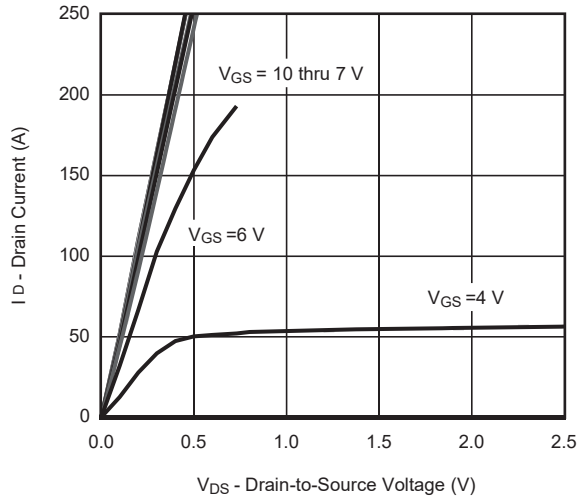
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

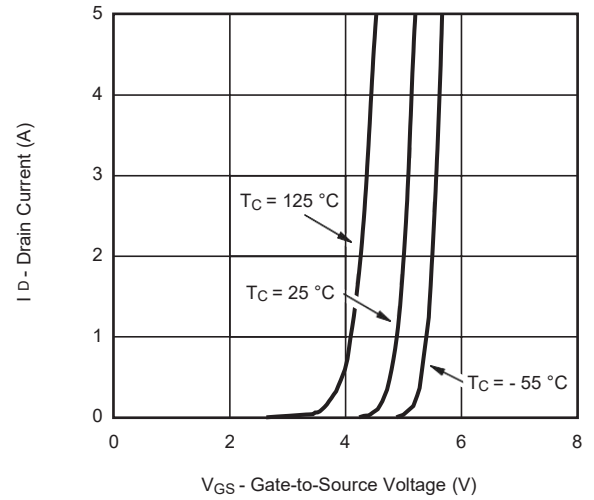
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

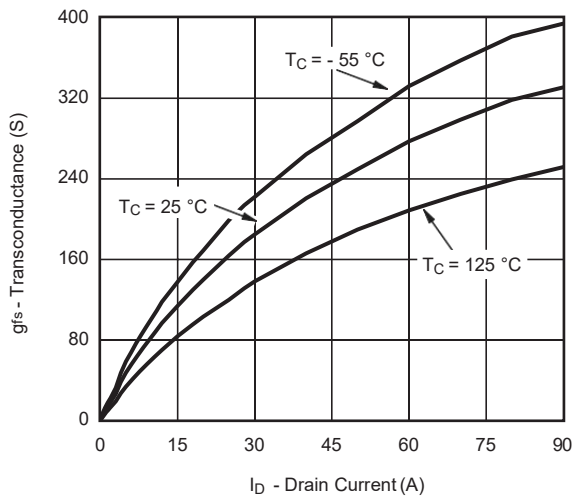
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



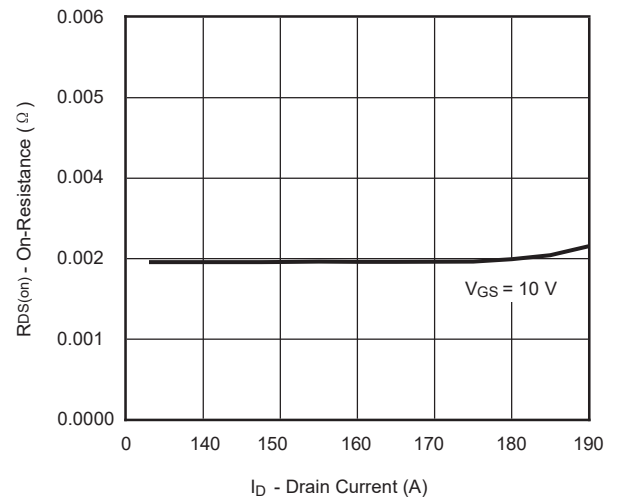
Output Characteristics



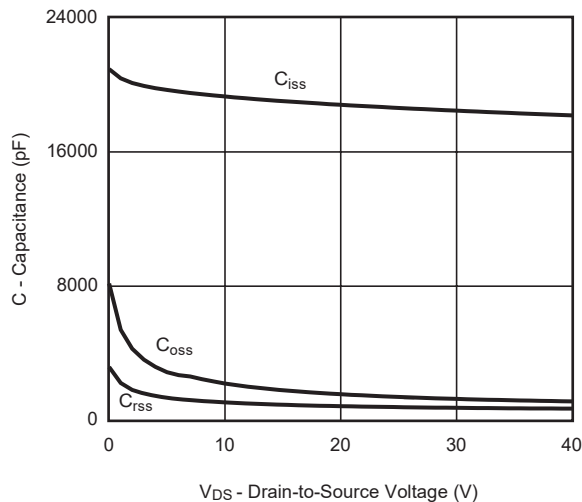
Transfer Characteristics



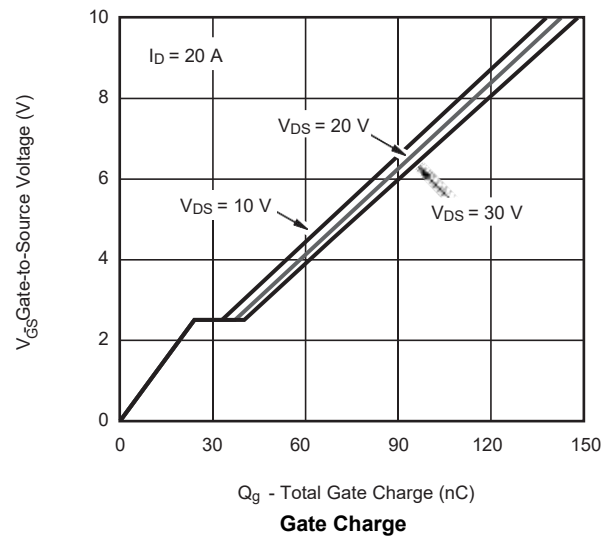
Transconductance



On-Resistance vs. Drain Current

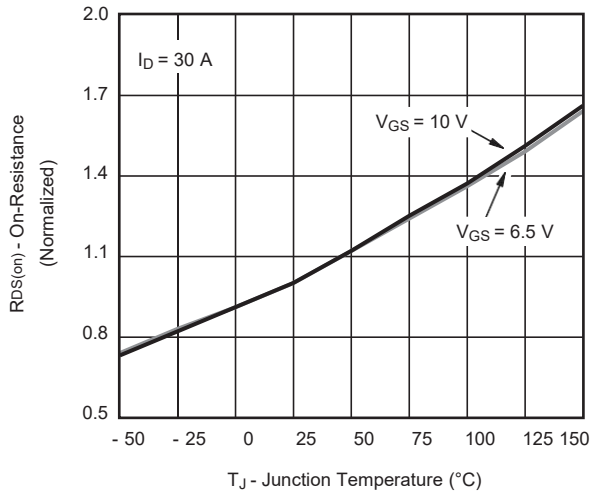


Capacitance

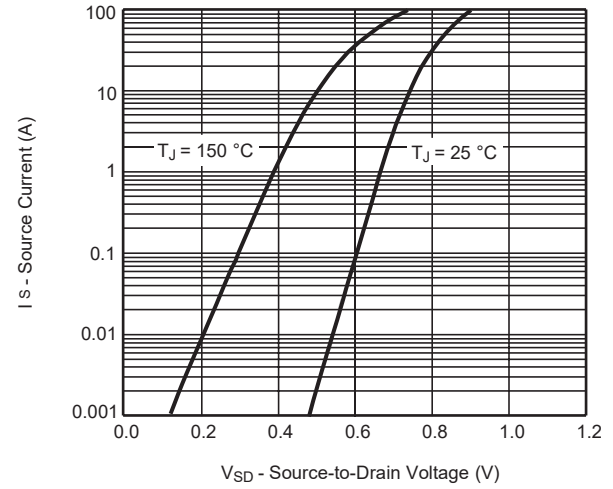


Gate Charge

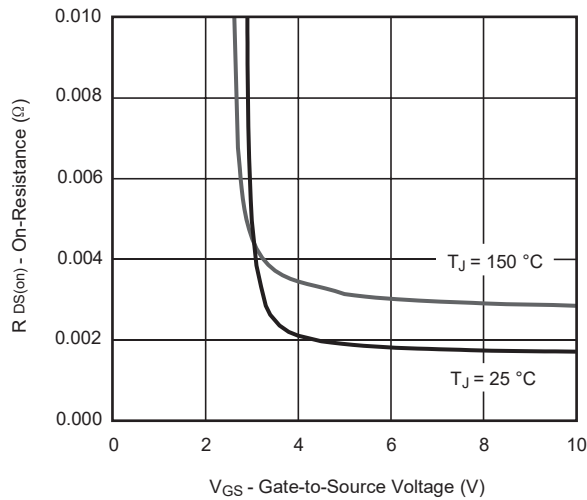
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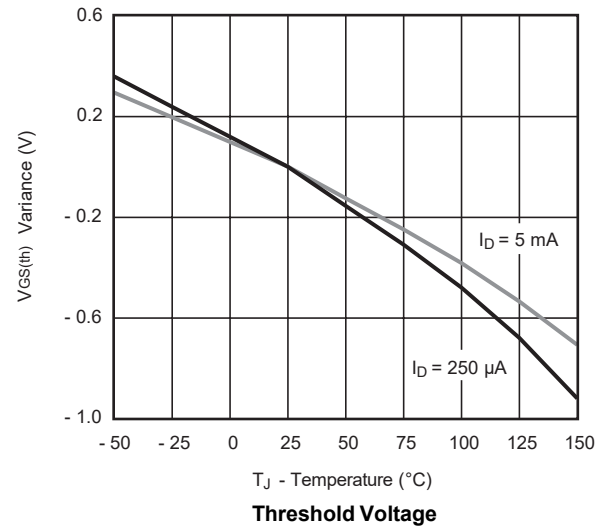
On-Resistance vs. Junction Temperature



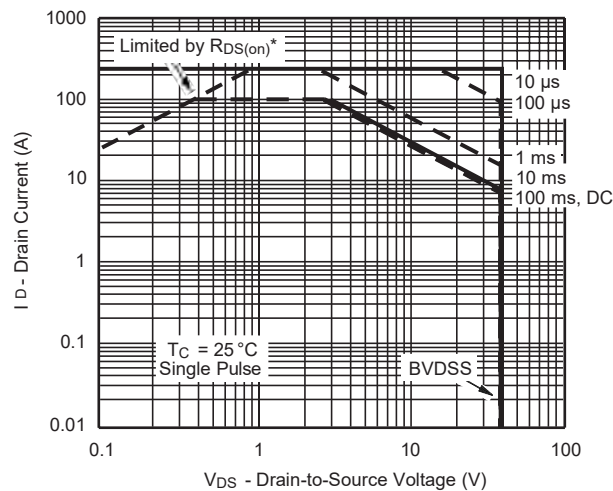
Forward Diode Voltage vs. Temperature



On-Resistance vs. Gate-to-Source Voltage



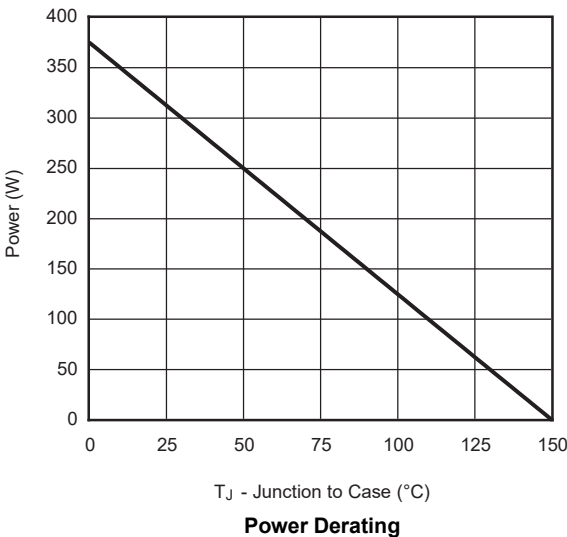
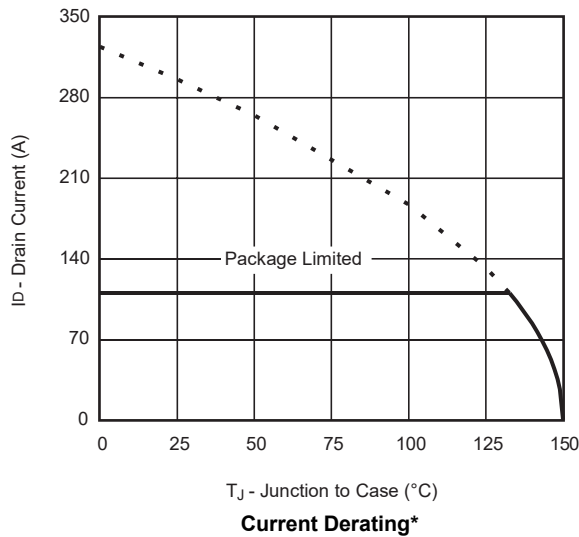
Threshold Voltage



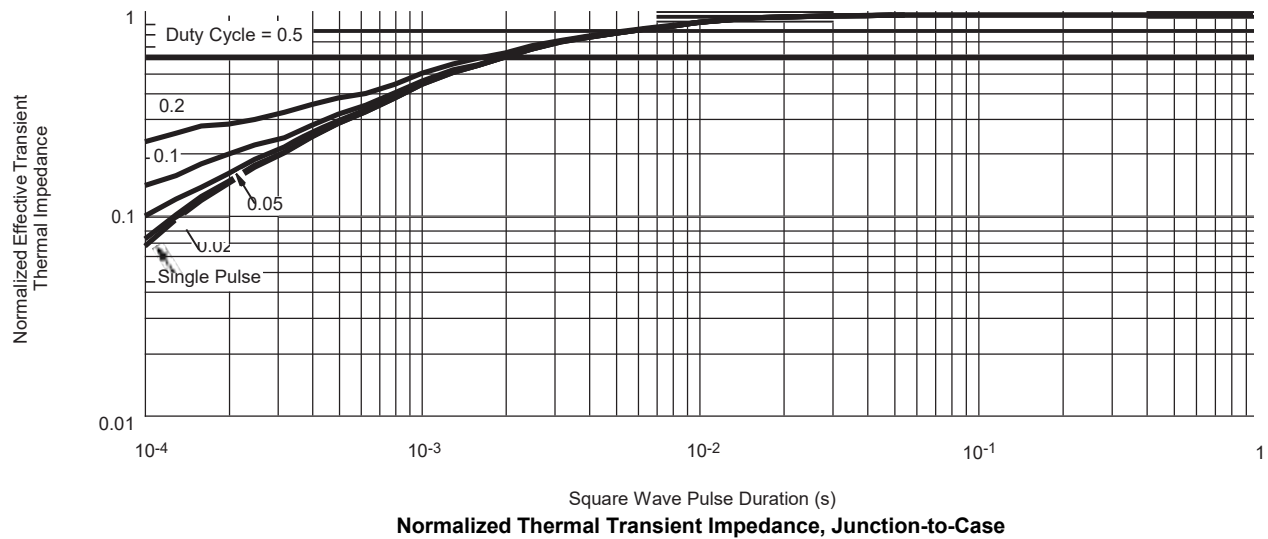
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

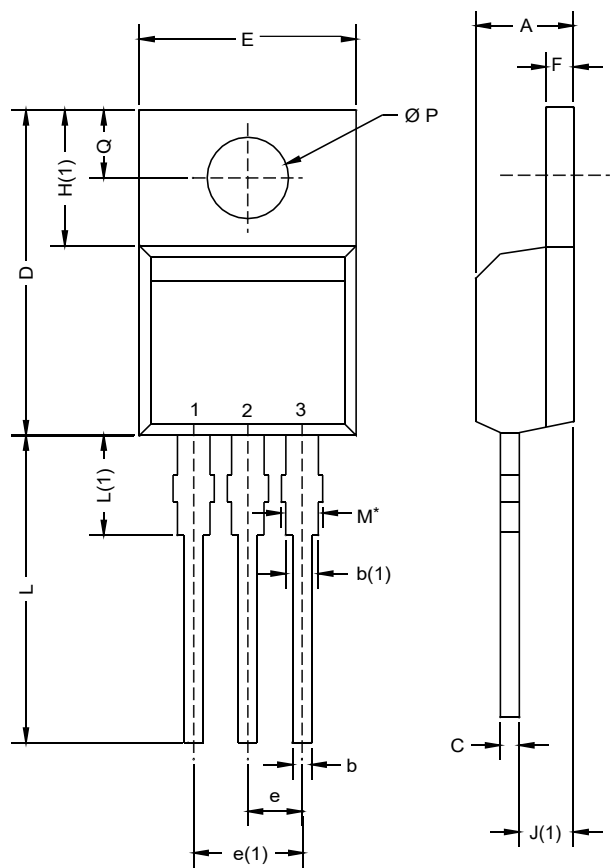
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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